



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C
100V	13.5mΩ @ V _{GS} = 10V	42A
	18mΩ @ V _{GS} = 6.0V	36A
	23.5mΩ @ V _{GS} = 4.5V	32A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

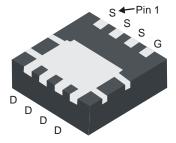
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- Excellent Q_{qd x} R_{DS (ON)} Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

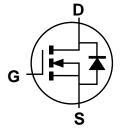
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Bottom View



Top View



Equivalent Circuit

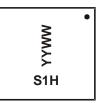
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMT10H015LFG-7	PowerDI3333-8	2,000/Tape & Reel	
DMT10H015LFG-13	PowerDI3333-8	3,000/Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



S1H = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V _{GSS}	±20	V
T _A = T _A =		I _D	10 8.0	А
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	42 26	А
Maximum Continuous Body Diode Forward Current (Note 5)	Is	1.5	Α	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I _{DM}	75	Α
Avalanche Current (L = 3mH)		I _{AS}	7.5	A
Avalanche Energy (L = 3mH)		E _{AS}	85	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

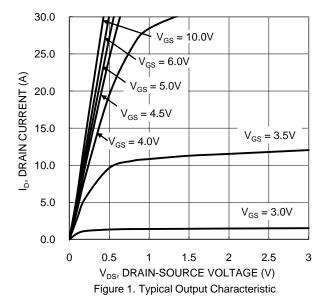
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	61	°C/W	
Total Power Dissipation $T_C = +25^{\circ}C$		P _D	35	W
Thermal Resistance, Junction to Case		$R_{ hetaJC}$	3.5	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	1.4	2.0	3.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		1	10.8	13.5		$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	I	13.3	18	mΩ	$V_{GS} = 6.0V, I_D = 20A$	
		l	17.9	23.5		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	I	0.9	1.3	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	1	1,871	_		$V_{DS} = 50V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	1	261	_	pF		
Reverse Transfer Capacitance	Crss	l	6.9	_			
Gate Resistance	R _G	I	0.75	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{g}	I	33.3	_		V 50V L 40A	
Gate-Source Charge	Q_{gs}		6.9	_	nC	$V_{DD} = 50V, I_D = 10A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_{gd}	l	5.1	_		VGS = 10V	
Turn-On Delay Time	t _{D(ON)}		6.5	_			
Turn-On Rise Time	t _R	_	7.0	_	ns	$\begin{split} V_{DD} &= 50 V, \ V_{GS} = 10 V, \\ I_D &= 10 A, \ R_G = 6 \Omega \end{split}$	
Turn-Off Delay Time	t _{D(OFF)}	_	19.7	_	115		
Turn-Off Fall Time	t _F	_	8.1	_			
Reverse Recovery Time	t _{RR}	-	37.9	_	ns	I_ = 10.0 di/dt = 100.0 /u.c	
Reverse Recovery Charge	Q _{RR}	_	51.9	_	nC	I _F = 10A, di/dt = 100A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to product testing.





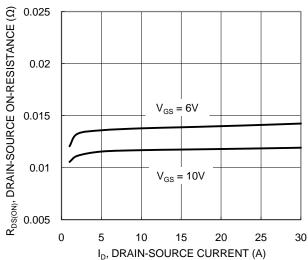


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

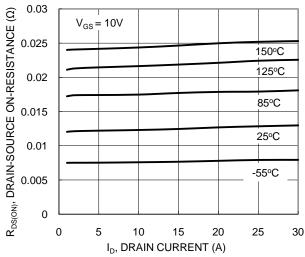
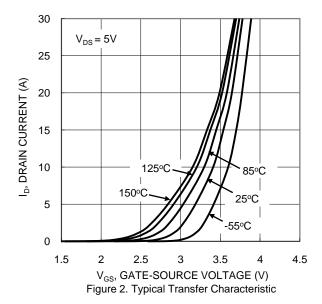


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



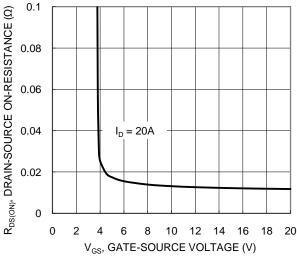


Figure 4. Typical Transfer Characteristic

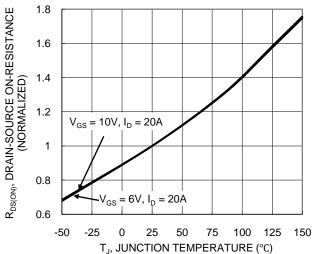


Figure 6. On-Resistance Variation with Junction Temperature





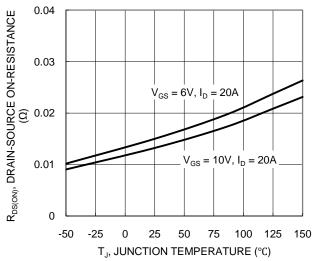


Figure 7. On-Resistance Variation with Junction Temperature

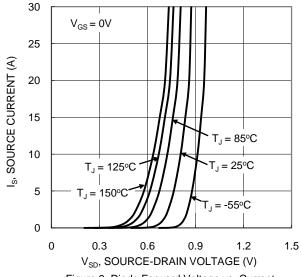


Figure 9. Diode Forward Voltage vs. Current

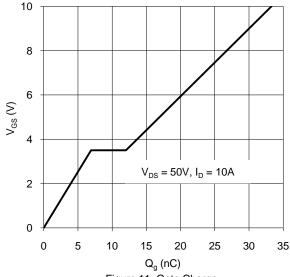


Figure 11. Gate Charge

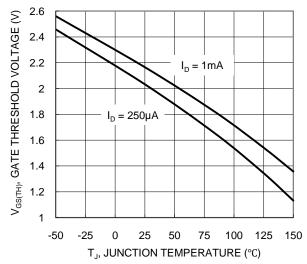
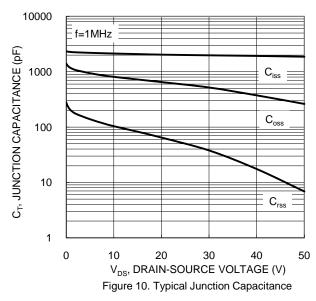


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} Limited 100 ID, DRAIN CURRENT (A) 10 1 ∰ Pw 0.1 T_C = 25 °C Single Pulse 0.01 DUT on 1*MRP Board DC $V_{GS} = 10V$ 0.001 0.01 10 100 1000 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



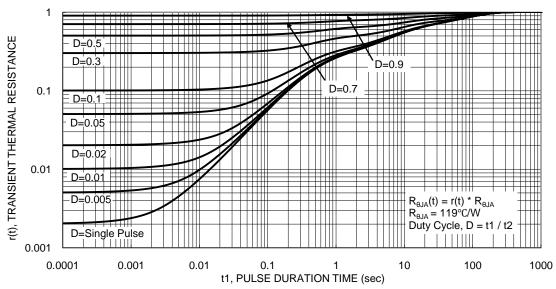


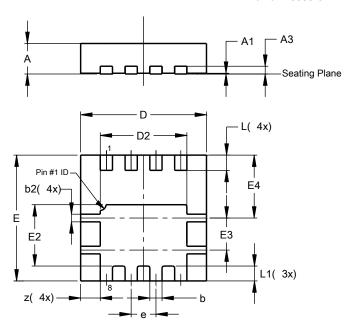
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

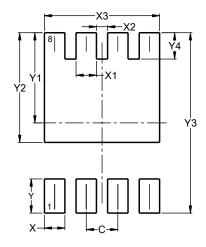


	PowerDI3333-8					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
А3	1	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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